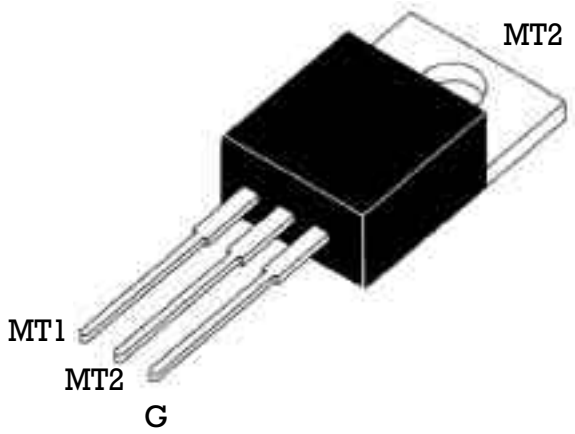
LOGIC LEVEL TRIAC

TO220-AB



On-State Current
4 Amp

Gate Trigger Current
≤ 5 mA to ≤ 10 mA

Off-State Voltage
200 V ÷ 600 V

This series of **TRIAC**s uses a high performance PNPN technology.

These parts are intended for general purpose AC switching applications with highly inductive loads.

Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Min.	Max.	Unit
$I_{T(RMS)}$	RMS On-state Current	All Conduction Angle, T_C = 110 °C		4	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 60 Hz		33	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 50 Hz		30	A
I^2t	Fusing Current	t_p = 10 ms, Half Cycle		4.5	A^2s
I_{GM}	Peak Gate Current	20 µs max. T_j =125°C		4	A
$P_{G(AV)}$	Average Gate Power Dissipation	T_j =125°C		1	W
di/dt	Critical rate of rise of on-state current	I_G = 2x I_{GT}, t_r ≤100ns f= 120 Hz, T_j =125°C	50		A/µs
T_j	Operating Temperature		-40	+125	°C
T_{stg}	Storage Temperature		-40	+150	°C

SYMBOL	PARAMETER	VOLTAGE			Unit
		B	D	M	
V_{DRM} V_{RRM}	Repetitive Peak Off State Voltage	200	400	600	V

LOGIC LEVEL TRIAC

Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	Quadrant		SENSITIVITY					Unit
					04	05	07	08	09	
I_{GT} (1)	Gate Trigger Current	V_D = 12 V_{DC}, R_L = 33Ω, T_j = 25 °C	Q1÷Q3	MAX	5	5	5	10	10	mA
		V_D = V_{DRM},	Q4	MAX		5	7		10	mA
I_{DRM} /I_{RRM}	Off-State Leakage Current	V_R = V_{RRM}, T_j = 125 °C		MAX	1					mA
		T_j = 25 °C		MAX	5					µA
V_{to} (2)	Threshold Voltage	T_j = 125 °C		MAX	0.9					V
R_d (2)	Dynamic Resistance	T_j = 125 °C		MAX	120					mΩ
V_{TM} (2)	On-state Voltage	I_T = 5.5 Amp, tp = 380 µs, T_j = 25 °C		MAX	1.6					V
V_{GT}	Gate Trigger Voltage	V_D = 12 V_{DC}, R_L = 33Ω, T_j = 25 °C	Q1÷Q4 (3)	MAX	1.3					V
V_{GD}	Gate Non Trigger Voltage	V_D = V_{DRM}, R_L = 3.3KΩ, T_j = 125 °C	Q1÷Q4 (3)	MIN	0.2					V
I_H (2)	Holding Current	I_T = 100 mA, Gate open, T_j = 25 °C		MAX	15	15	10	15	20	mA
I_L	Latching Current	I_G = 1.2 I_{GT}, T_j = 25 °C	Q1,Q3,Q4 (4)	MAX	10	10	10	25	20	mA
			Q2	MAX	20	20	15	30	40	
dv / dt (2)	Critical Rate of Voltage Rise	V_D = 0.67 x V_{DRM}, Gate open T_j = 125 °C		MIN	10	10	20	40	20	V/µs
(di/dt)c (2)	Critical Rate of Current Rise	(dv/dt)c= 0.1 V/µs T_j = 125 °C		MIN	1.5	1.5	1.8	2.7	2.5	A/ms
		(dv/dt)c= 10 V/µs T_j = 125 °C		MIN	-	-	0.9	2.0	-	
		without snubber Tj = 125 °C		MIN	-	-	-	-	-	
$R_{th(j-c)}$	Thermal Resistance Junction-Case				2.6					°C/W
$R_{th(j-a)}$	Thermal Resistance Junction-Ambient				60					°C/W

(1) Minimum I_{GT} is guaranted at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

(3) Q4 for 4 Quadrant Triacs
Q3 for 3 Quadrant Triacs

(4) Only for 4 Quadrant Triacs

PART NUMBER INFORMATION

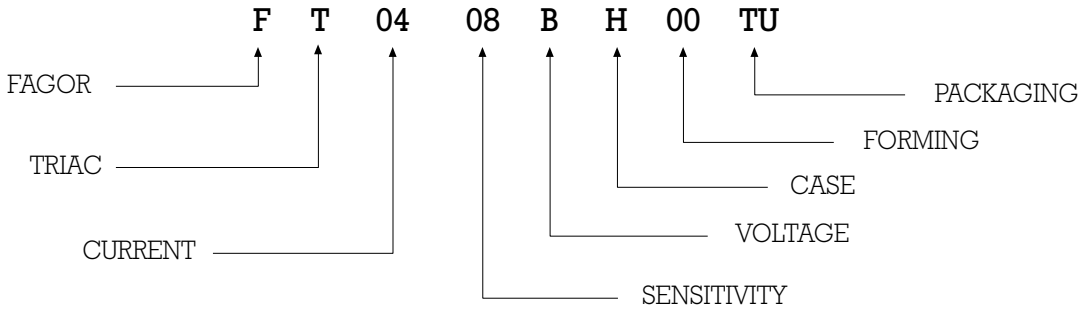


Fig. 1: Maximum power dissipation versus RMS on-state curren (full cycle).

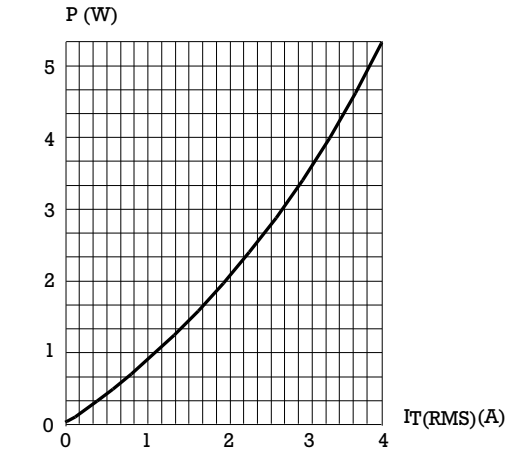


Fig. 2: RMS on-state current versus case temperature (full cycle).

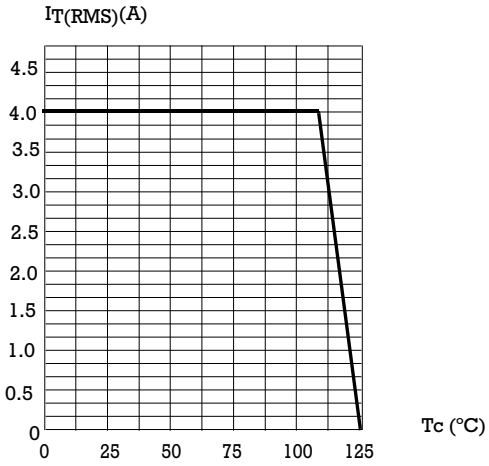


Fig. 3: : Relative variation of thermal impedance versus pulse duration.

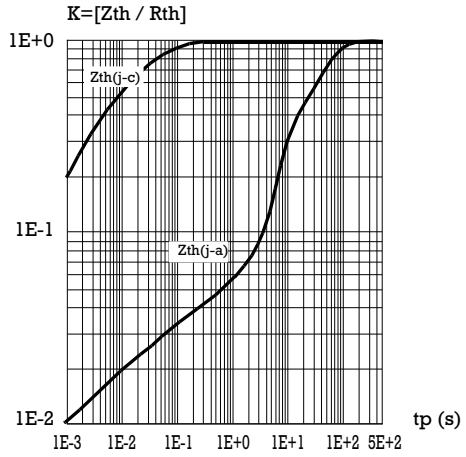


Fig. 4: On-state characteristics (maximum values)

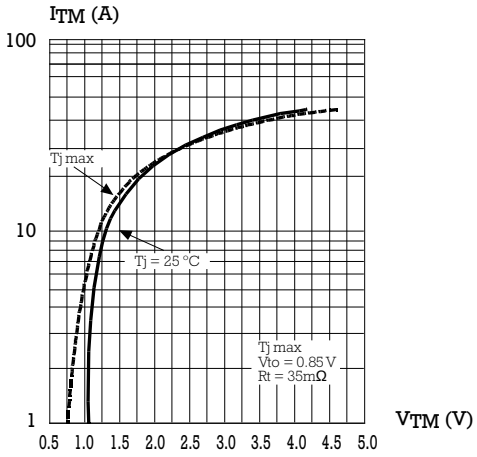


Fig. 5: Surge peak on-state current versus number of cycles

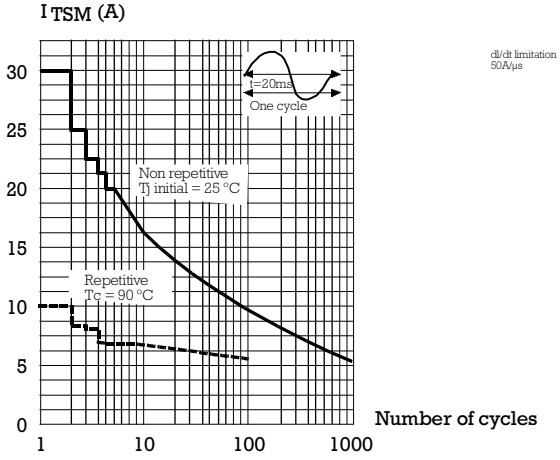


Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<10ms, and corresponding value of I²t.

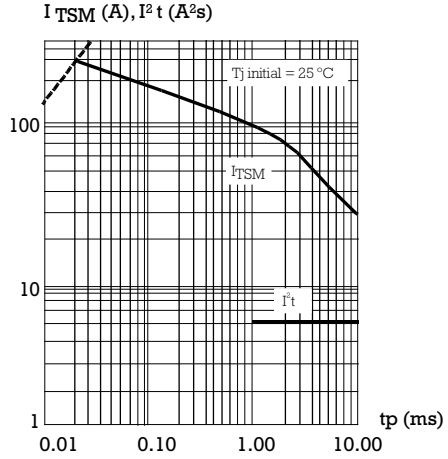


Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

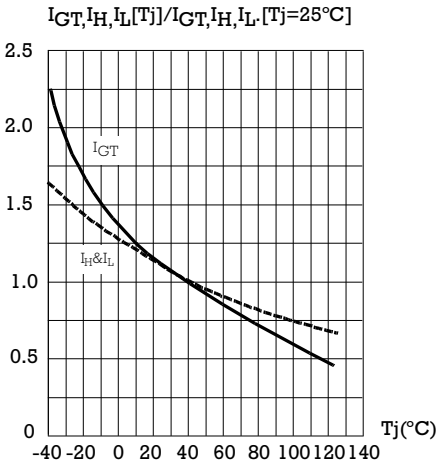
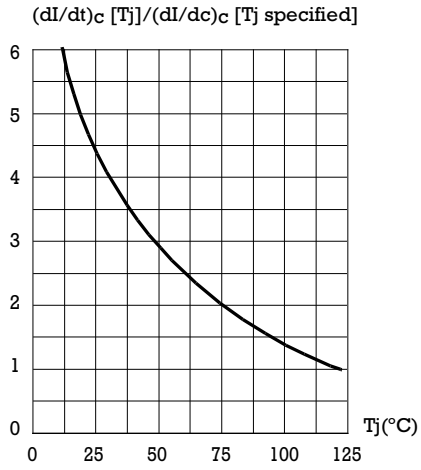
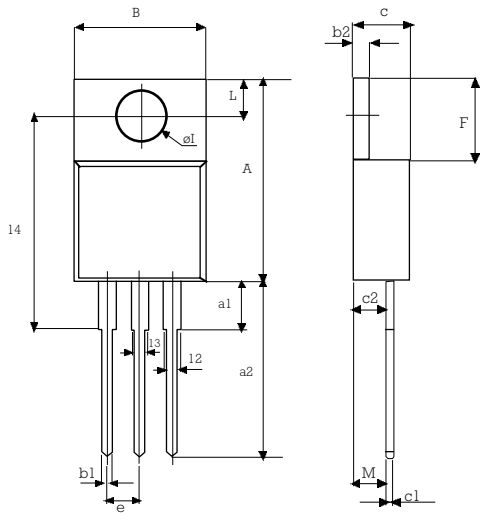


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature



PACKAGE MECHANICAL DATA TO-220AB (Plastic)



REF.	DIMENSIONS		
	Milimeters		
	Min.	Nominal	Max.
A	15.20		15.90
a1		3.75	
a2	13.00		14.00
B	10.00		10.40
b1	0.61		0.88
b2	1.23		1.32
C	4.40		4.60
c1	0.49		0.70
c2	2.40		2.72
e	2.40		2.70
F	6.20		6.60
I	3.75		3.85
I4	15.80	16.40	16.80
L	2.65		2.95
I2	1.14		1.70
I3	1.14		1.70
M		2.60	